

Pb Free Plating Product

DSEE15-04CC thru DSEE15-24CC



15.0 Ampere Insulated Dual Tandem Structure In Series Ultra Fast Recovery Rectifiers

<p>Features</p> <ul style="list-style-type: none"> ThinkSemi latest&matured process FRD/FRED Low forward voltage drop High current capability Low reverse leakage current High surge current capability <p>Application</p> <ul style="list-style-type: none"> Automotive Inverters and Solar Inverters Car Audio Amplifiers and Sound Device Systems Plating Power Supply, Motor Control, UPS and SMPS etc. <p>Mechanical Data</p> <ul style="list-style-type: none"> Case: Isolated fully plastic ITO-220AB/TO-220F-3L package Epoxy: UL 94V-0 rate flame retardant Terminals: Solderable per MIL-STD-202 method 208 Polarity: As marked on diode body Mounting position: Any Weight: 2.0 gram approximately 	<p>ITO-220AB/TO-220F-3L</p> <p>Unit: inch(mm)</p>
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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.
 Single phase, half wave, 60Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

PARAMETER	SYMBOL	DSEE15-04CC	DSEE15-08CC	DSEE15-12CC	DSEE15-16CC	DSEE15-20CC	DSEE15-24CC	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	200x2	400x2	600x2	800x2	1000x2	1200x2	V
Maximum RMS Voltage	VRMS	140x2	280x2	420x2	560x2	700x2	840x2	V
Maximum DC Blocking Voltage	VDC	200x2	400x2	600x2	800x2	1000x2	1200x2	V
Maximum Average Forward Rectified Current TC=125°C (Total Device 2x15.0A=30.0A)	IF(AV)	15.0						A
Peak Forward Surge Current, 8.3ms single Half sine-wave superimposed on rated load (JEDEC method)(Per Diode/Per Leg)	IFSM	300						A
Maximum Instantaneous Forward Voltage @15.0A(Per Diode/Per Leg)	VF (Typical)	0.85-0.95	1.00-1.25	1.25-1.50	1.50-1.70			V
Maximum DC Reverse Current @TJ=25°C At Rated DC Blocking Voltage @TJ=125°C	IR	1.0 100						µA µA
Maximum Reverse Recovery Time (Note1)	Trr	25-50			50-75			nS
Typical Junction Capacitance (Note 2)	CJ	150						pF
Typical Thermal Resistance (Note 3)	RθJC	3.0						°C/W
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 to +175						°C

Note:(1)Reverse recovery test conditions IF = 0.5A, IR = 1.0A, Irr = 0.25A.
 Note:(2)Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts DC.
 Note:(3)Thermal Resistance junction to case.

FIG.1 - FORWARD CURRENT DERATING CURVE

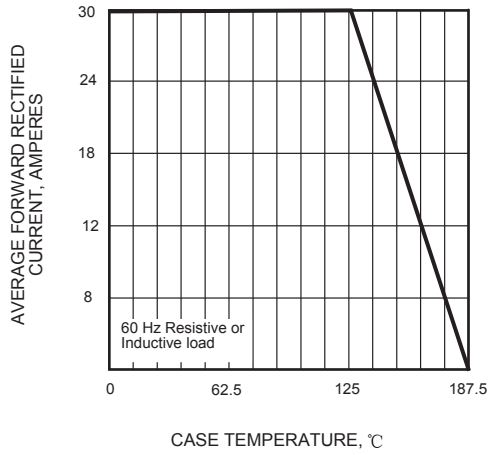


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

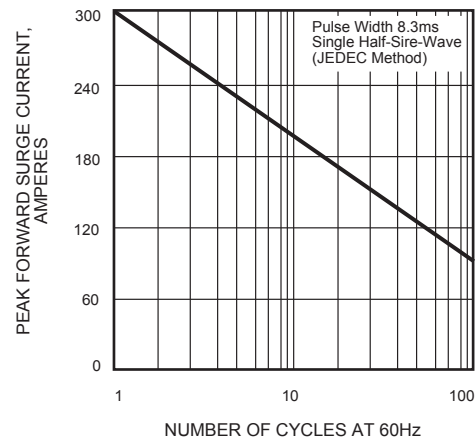


FIG.3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

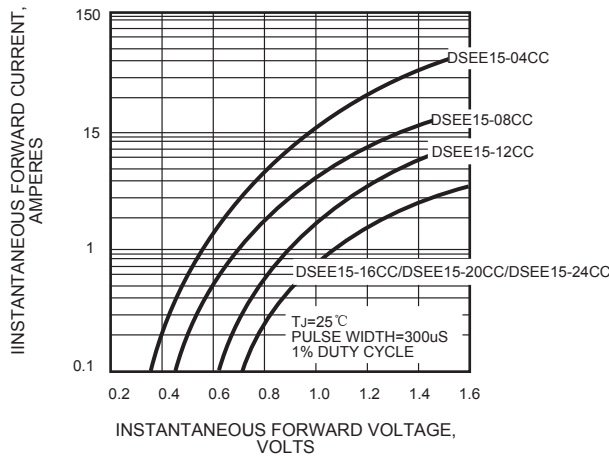


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

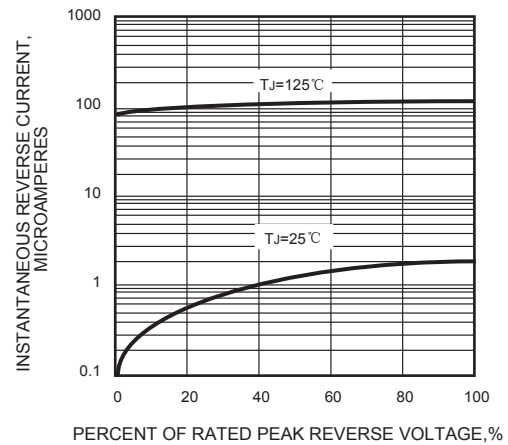


FIG.5 - TYPICAL JUNCTION CAPACITANCE

